

**Silicon Bridge
Rectifier**

$$V_{RRM} = 50 \text{ V} - 1000 \text{ V}$$

$$I_F = 50 \text{ A}$$

Features

- High efficiency
- Types up to 1000 V V_{RRM}
- Silicon junction
- Metal case

Mechanical Data

Case: Mounted in the bridge encapsulation

Mounting position: Hole for #10 screw

Polarity: Marked on case

KBPC-T/W Package


Maximum ratings, at $T_J = 25 \text{ }^\circ\text{C}$, unless otherwise specified (KBPCXXXXT uses KBPC-T package while KBPCXXXXW uses KBPC-W package)

Parameter	Symbol	Conditions	KBPC5006T/W	KBPC5008T/W	KBPC5010T/W	Unit
Repetitive peak reverse voltage	V_{RRM}		600	800	1000	V
RMS reverse voltage	V_{RMS}		420	560	700	V
DC blocking voltage	V_{DC}		600	800	1000	V
Continuous forward current	I_F	$T_C \leq 40 \text{ }^\circ\text{C}$	50	50	50	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25 \text{ }^\circ\text{C}$, $t_p = 8.3 \text{ ms}$	400	400	400	A
Operating temperature	T_J		-55 to 150	-55 to 150	-55 to 150	$^\circ\text{C}$
Storage temperature	T_{stg}		-55 to 150	-55 to 150	-55 to 150	$^\circ\text{C}$

Electrical characteristics, at $T_J = 25 \text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	KBPC5006T/W	KBPC5008T/W	KBPC5010T/W	Unit
Diode forward voltage	V_F	$I_F = 25 \text{ A}$, $T_J = 25 \text{ }^\circ\text{C}$	1.1	1.1	1.1	V
Reverse current	I_R	$V_R = 50 \text{ V}$, $T_J = 25 \text{ }^\circ\text{C}$	5	5	5	μA
		$V_R = 50 \text{ V}$, $T_J = 100 \text{ }^\circ\text{C}$	500	500	500	
Thermal resistance, junction - case	$R_{\theta JC}$		2.5	2.5	2.5	$^\circ\text{C/W}$

